

## **High Voltage Phase Control Thyristor, 12 A**



3L TO-220AB

PRIMARY CHARACTERISTICS								
I <sub>T(AV)</sub>	8 A							
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V							
V <sub>TM</sub>	1.2 V							
l <sub>GT</sub>	15 mA							
T <sub>J</sub>	-40 °C to 125 °C							
Package	3L TO-220AB							
Circuit configuration	Single SCR							

#### **FEATURES**

- Designed and qualified according to JEDEC®-JESD 47
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



#### **APPLICATIONS**

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge.

#### **DESCRIPTION**

The VS-12TTS08... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS									
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS									
Capacitive input filter T <sub>A</sub> = 55 °C, T <sub>J</sub> = 125 °C, common heatsink of 1 °C/W	13.5	17	А						

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS						
I <sub>T(AV)</sub>	Sinusoidal waveform	8	Α						
I <sub>T(RMS)</sub>		12.5	^						
V <sub>DRM</sub> /V <sub>RRM</sub>		800	V						
I <sub>TSM</sub>		110	A						
V <sub>T</sub>	8 A, T <sub>J</sub> = 25 °C	1.2	V						
dV/dt		150	V/µs						
dl/dt		100	A/μs						
T <sub>J</sub>	Range	-40 to +125	°C						

VOLTAGE RATINGS									
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA						
VS-12TTS08-M3	800	800	1.0						



ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TES	T CONDITIONS	VALUES	UNITS			
Maximum average on-state current	I <sub>T(AV)</sub>	T 100 °C 100° o	8					
Maximum RMS on-state current	I <sub>T(RMS)</sub>	1 <sub>C</sub> = 106 C, 180 C	conduction, half sine wave	12.5	Α			
Maximum peak, one-cycle,	l	10 ms sine pulse, ra	95	A				
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no	o voltage reapplied, T <sub>J</sub> = 125 °C	110				
Maximum I <sup>2</sup> t for fusing	I <sup>2</sup> t	10 ms sine pulse, ra	ated V <sub>RRM</sub> applied, T <sub>J</sub> = 125 °C	45	A 2-			
Maximum i-t for fusing	1-1	10 ms sine pulse, no	64	A <sup>2</sup> s				
Maximum $I^2\sqrt{t}$ for fusing	I <sup>2</sup> √t	t = 0.1  ms to  10  ms,	$t = 0.1$ ms to 10 ms, no voltage reapplied, $T_J = 125$ °C					
Maximum on-state voltage drop	$V_{TM}$	8 A, T <sub>J</sub> = 25 °C	8 A, T <sub>J</sub> = 25 °C					
On-state slope resistance	r <sub>t</sub>	T <sub>.l</sub> = 125 °C	T 105 90		mΩ			
Threshold voltage	V <sub>T(TO)</sub>	1J = 125 C		0.87	V			
Maximum reverse and direct leakage	l=/l=	T <sub>J</sub> = 25 °C	= Rated V <sub>RRM</sub> /V <sub>DRM</sub>	0.05				
current	I <sub>RM</sub> /I <sub>DM</sub>	T <sub>J</sub> = 125 °C	- nateu v <sub>RRM</sub> / v <sub>DRM</sub>	1.0				
Typical holding current	I <sub>H</sub>	Anode supply = 6 V $T_J = 25  ^{\circ}C$	30	mA				
Maximum latching current	IL	Anode supply = 6 V	50					
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear}$	T <sub>J</sub> = T <sub>J</sub> max., linear to 80 °C, V <sub>DRM</sub> = R <sub>g</sub> - k = Open					
Maximum rate of rise of turned-on current	dl/dt			100	A/µs			

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P <sub>GM</sub>		8.0	W	
Maximum average gate power	P <sub>G(AV)</sub>		2.0	VV	
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α	
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V	
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 65 °C	20		
Maximum required DC gate current to trigger	I <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	15	mA	
990		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	10		
		Anode supply = 6 V, resistive load, $T_J$ = - 65 °C	1.2		
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	1	V	
rollage to trigge.		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	0.7	V	
Maximum DC gate voltage not to trigger	$V_{GD}$	T = 105 °C V = Poted value	0.2	1	
Maximum DC gate current not to trigger	I <sub>GD</sub>	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value	0.1	mA	

SWITCHING								
PARAMETER SYMBOL TEST CONDITIONS VALUES								
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.8					
Typical reverse recovery time	t <sub>rr</sub>	T 105 °C	3	μs				
Typical turn-off time	t <sub>q</sub>	T <sub>J</sub> = 125 °C	100					



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### Vishay Semiconductors

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum junction and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>		-40 to 125	°C		
Maximum thermal resistance, junction to case		R <sub>thJC</sub>	DC operation	1.5			
Maximum thermal resistance, junction to ambient		R <sub>thJA</sub>		62	°C/W		
Typical thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, smooth and greased	0.5			
Approximate weight				2	g		
Approximate weight				0.07	oz.		
Mounting torque	minimum			6 (5)	kgf · cm		
Mounting torque	maximum			12 (10)	(lbf · in)		
Marking device			Case style 3L TO-220AB	12T	TS08		

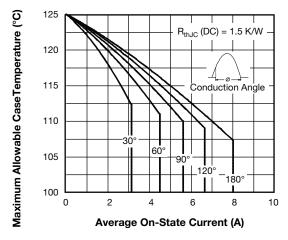


Fig. 1 - Current Ratings Characteristics

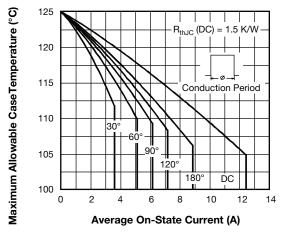


Fig. 2 - Current Ratings Characteristics

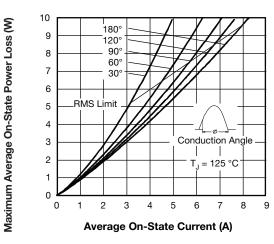


Fig. 3 - On-State Power Loss Characteristics

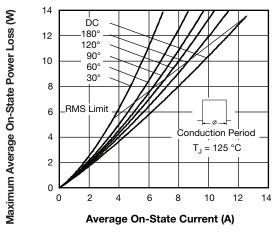


Fig. 4 - On-State Power Loss Characteristics

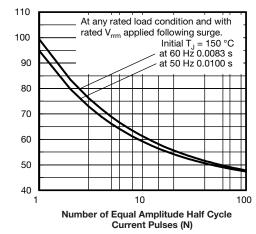


Fig. 5 - Maximum Non-Repetitive Surge Current

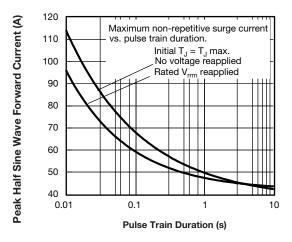


Fig. 6 - Maximum Non-Repetitive Surge Current

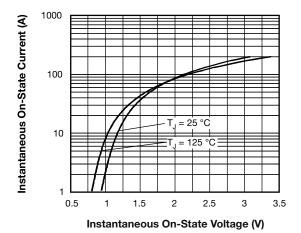


Fig. 7 - On-State Voltage Drop Characteristics

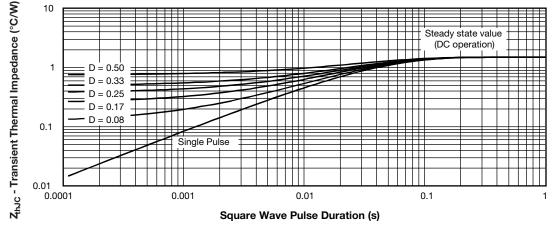
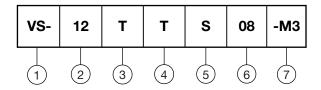


Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristics



### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - Current ratings (12 = 12.5 A)

3 - Circuit configuration:

T = single thyristor

4 - Package:

T = TO-220

5 - Type of silicon

S = standard recovery rectifier

6 - Voltage rating (08 = 800 V)

7 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

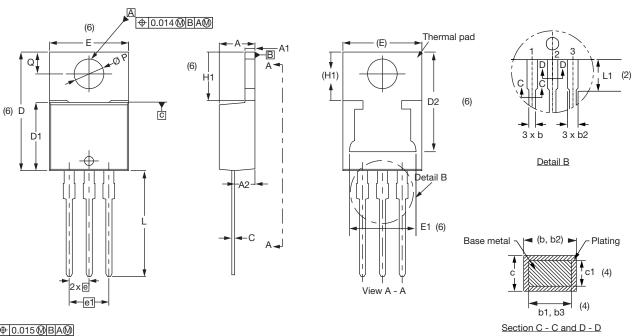
ORDERING INFORMATION (Example)								
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION								
VS-12TTS08-M3	50	1000	Antistatic plastic tubes					

LINKS TO RELATED DOCUMENTS						
Dimensions <u>www.vishay.com/doc?96154</u>						
Part marking information	www.vishay.com/doc?95028					

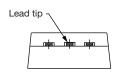


### **3L TO-220AB**

#### **DIMENSIONS** in millimeters and inches



#### **⊕** 0.015 **M** B A **M**



Conforms to JEDEC® outline TO-220AB

SYMBOL	MILLIM	IETERS	INC	HES	NOTES	NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183			D2	11.68	13.30	0.460	0.524	6, 7
A1	1.14	1.40	0.045	0.055			E	10.11	10.51	0.398	0.414	3, 6
A2	2.50	2.92	0.098	0.115			E1	6.86	8.89	0.270	0.350	6
b	0.69	1.01	0.027	0.040			е	2.41	2.67	0.095	0.105	
b1	0.38	0.97	0.015	0.038	4		e1	4.88	5.28	0.192	0.208	
b2	1.20	1.73	0.047	0.068			H1	6.09	6.48	0.240	0.255	6
b3	1.14	1.73	0.045	0.068	4		L	13.52	14.02	0.532	0.552	
С	0.36	0.61	0.014	0.024			L1	3.32	3.82	0.131	0.150	2
c1	0.36	0.56	0.014	0.022	4		ØΡ	3.54	3.91	0.139	0.154	
D	14.85	15.35	0.585	0.604	3		Q	2.60	3.00	0.102	0.118	
D1	8.38	9.02	0.330	0.355		1		•			•	

### **Notes**

- <sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- (7) Outline conforms to JEDEC® TO-220, except D2



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